ALPHA & OMEGA SEMICONDUCTOR

AO4466
N-Channel Enhancement Mode Field Effect Transistor

General Description

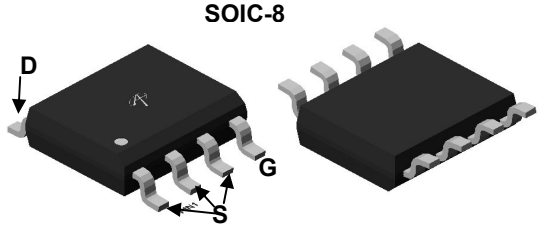
The AO4466/L uses advanced trench technology to provide excellent $R_{DS(ON)}$ and low gate charge. This device is suitable for use as a load switch or in PWM applications. The source leads are separated to allow a Kelvin connection to the source, which may be used to bypass the source inductance.
AO4466 and AO4466L are electrically identical.
-RoHS Compliant
-AO4466L is Halogen Free

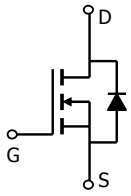
Features

V_{DS} (V) = 30V
I_D = 9.4A (V_{GS} = 10V)
$R_{DS(ON)}$ < 23mΩ (V_{GS} = 10V)
$R_{DS(ON)}$ < 35mΩ (V_{GS} = 4.5V)

100% UIS Tested!
100% Rg Tested!

SOIC-8





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	±20	V
Continuous Drain Current [AF]	T_A=25°C	I_D	9.4	A
	T_A=70°C		7.7	
Pulsed Drain Current [B]		I_{DM}	50	
Power Dissipation	T_A=25°C	P_D	3.1	W
	T_A=70°C		2.1	
Avalanche Current [B, G]		I_{AR}	18	A
Repetitive avalanche energy 0.1mH [B, G]		E_{AR}	16	mJ
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	34	40	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		62	75	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	18	24	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=250µA, V_{GS}=0V	30			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=30 V_{GS}=0V			1	µA
		T_J=55°C			5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}= ±20V			100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=250µA	1	1.6	3	V
$I_{D(ON)}$	On state drain current	V_{GS}=4.5V, V_{DS}=5V	20			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=10V, I_D=9.4A		17	23	mΩ
		T_J=125°C		24	30	
		V_{GS}=4.5V, I_D=5A		27	35	mΩ
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=9.4A	10	24		S
V_{SD}	Diode Forward Voltage	I_S=1A,V_{GS}=0V		0.75	1	V
I_S	Maximum Body-Diode Continuous Current				4.3	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=15V, f=1MHz		621	820	pF
C_{oss}	Output Capacitance			118		pF
C_{rss}	Reverse Transfer Capacitance			85	119	pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz	0.4	0.8	1.5	Ω
SWITCHING PARAMETERS						
Q_g(10V)	Total Gate Charge	V_{GS}=10V, V_{DS}=15V, I_D=9.4A		11.3	17	nC
Q_g(4.5V)	Total Gate Charge			5.7	8	nC
Q_{gs}	Gate Source Charge			2.1		nC
Q_{gd}	Gate Drain Charge			3		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=10V, V_{DS}=15V, R_L=1.6Ω, R_{GEN}=3Ω		4.5	6.5	ns
t_r	Turn-On Rise Time			3.1	5	ns
$t_{D(off)}$	Turn-Off DelayTime			15.1	23	ns
t_f	Turn-Off Fall Time			2.7	5	ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=9.4A, dI/dt=100A/µs		15.5	21	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=9.4A, dI/dt=100A/µs		7.1		nC
t_{rr}	Body Diode Reverse Recovery Time	I_F=9.4A, dI/dt=500A/µs		8.1	11	ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=9.4A, dI/dt=500A/µs		10.8		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6 are obtained using <300 µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

F. The current rating is based on the t≤ 10s junction to ambient thermal resistance rating.

G: L=100uH, V_{DD}=0V, R_G=0Ω, rated V_{DS}=30V and V_{GS}=10V

Rev 6: Aug 2008

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

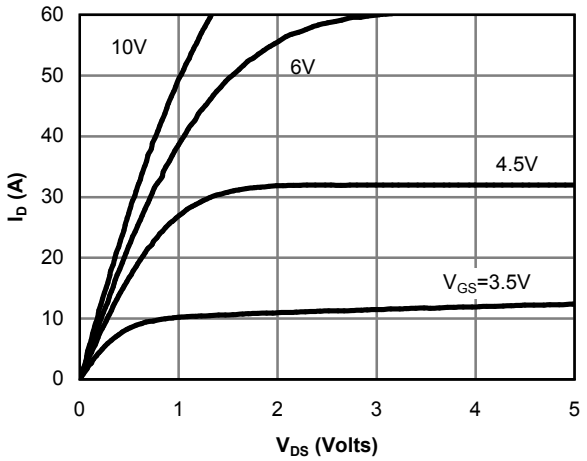


Fig 1: On-Region Characteristics

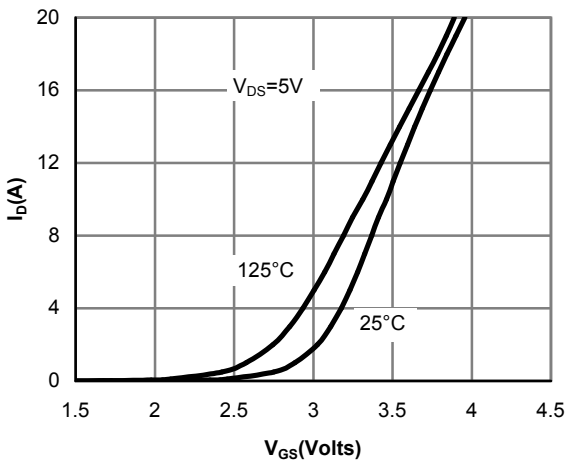


Figure 2: Transfer Characteristics

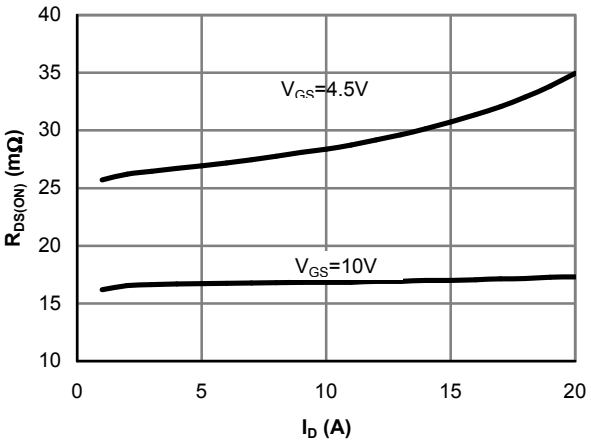


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

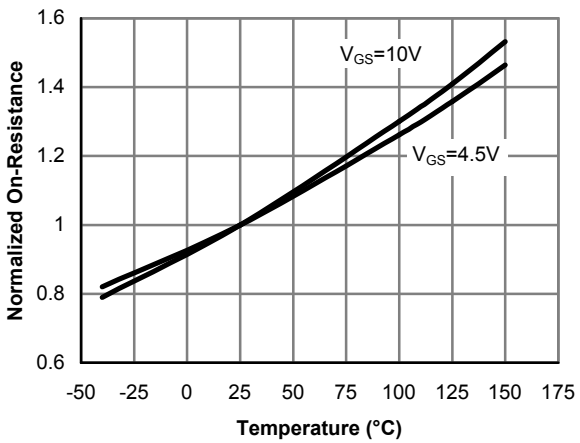


Figure 4: On-Resistance vs. Junction Temperature

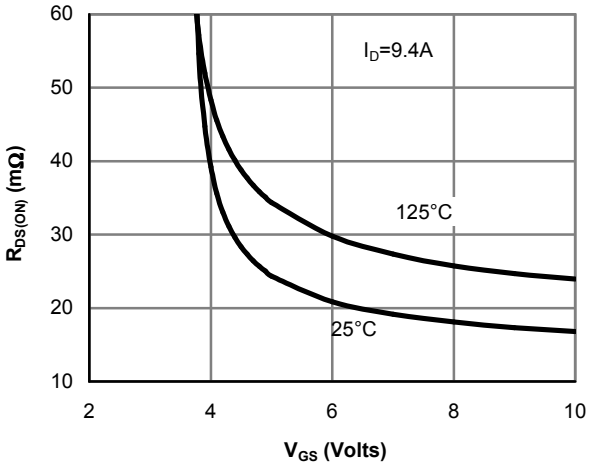


Figure 5: On-Resistance vs. Gate-Source Voltage

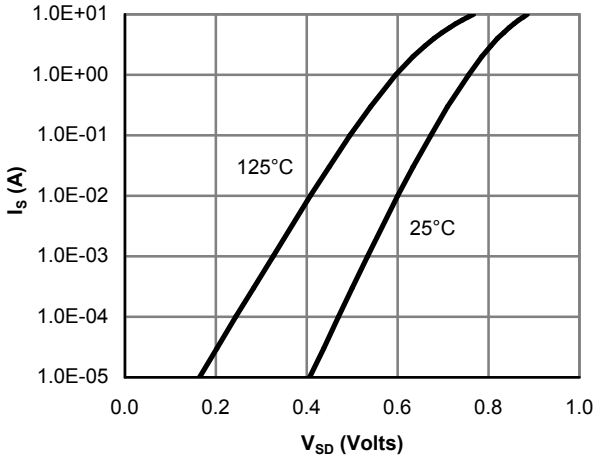


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

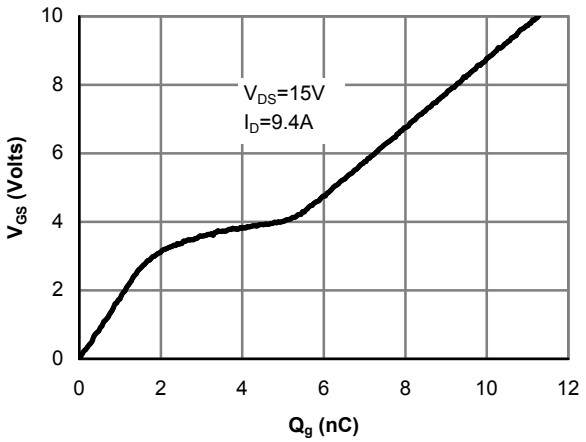


Figure 7: Gate-Charge Characteristics

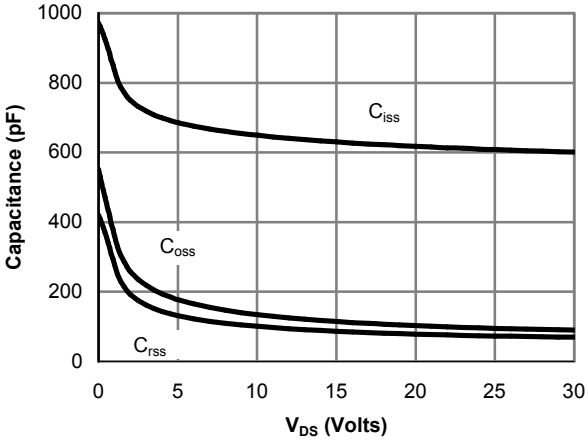


Figure 8: Capacitance Characteristics

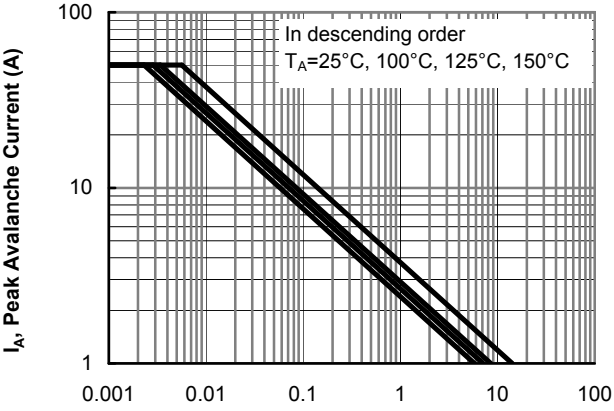


Figure 9: Single Pulse Avalanche Capability

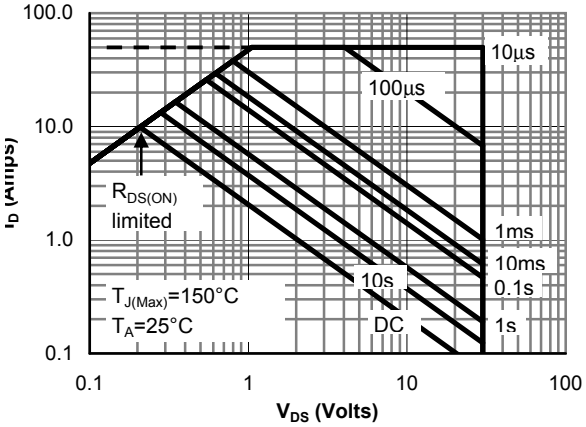


Figure 10: Maximum Forward Biased Safe Operating Area (Note E)

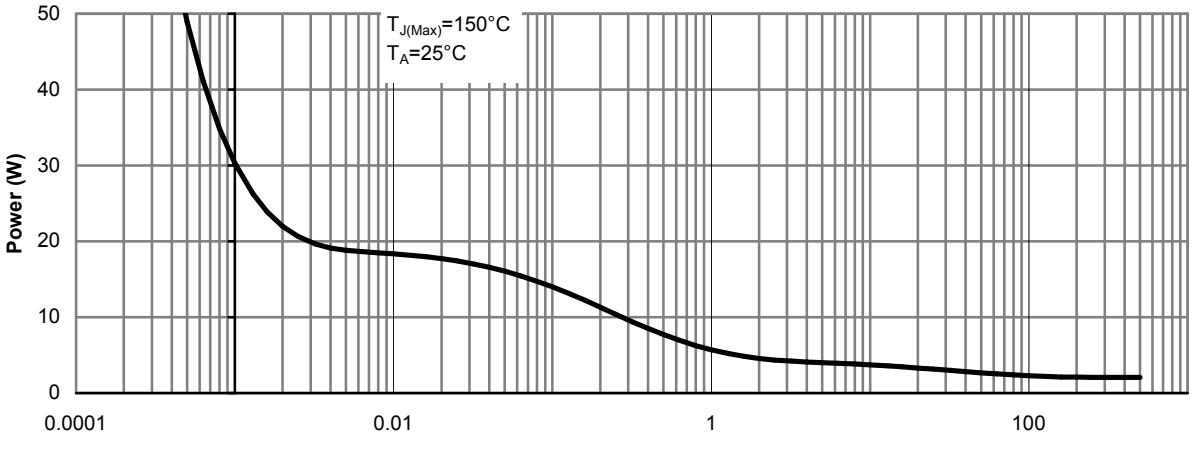


Figure 11: Single Pulse Power Rating Junction-to-Ambient (Note E)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

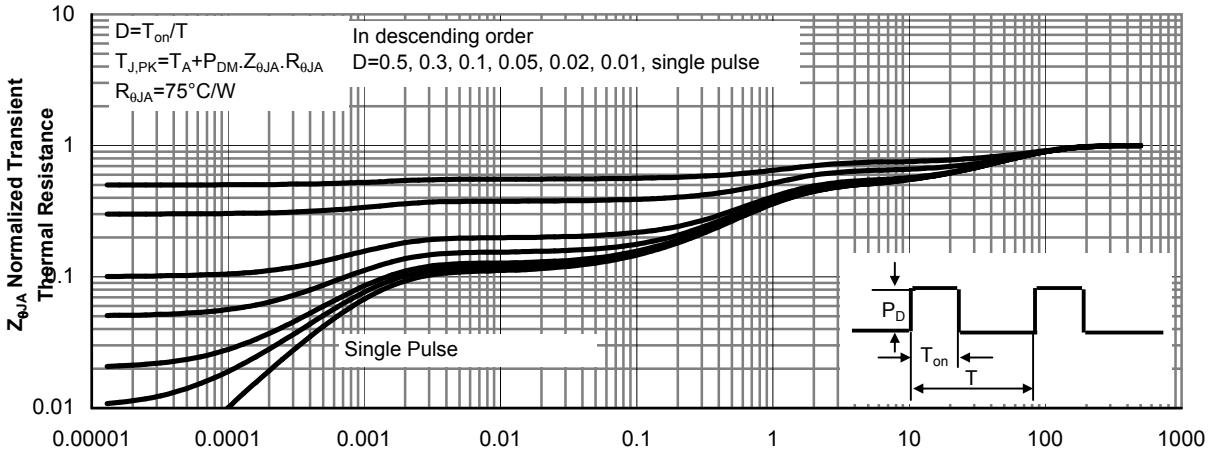
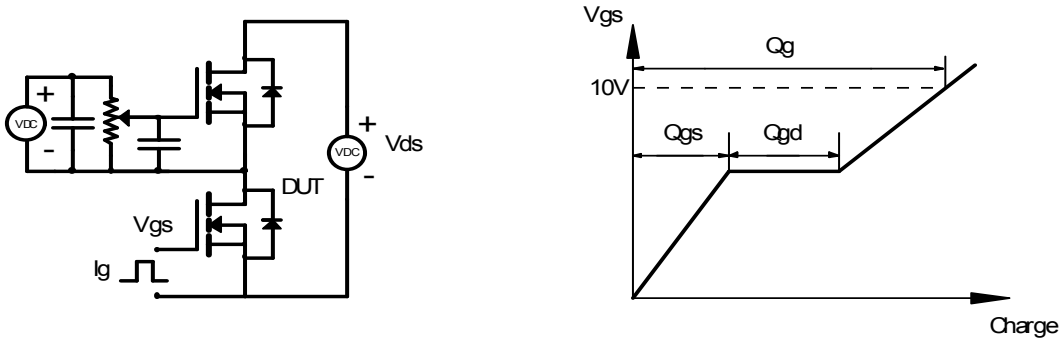
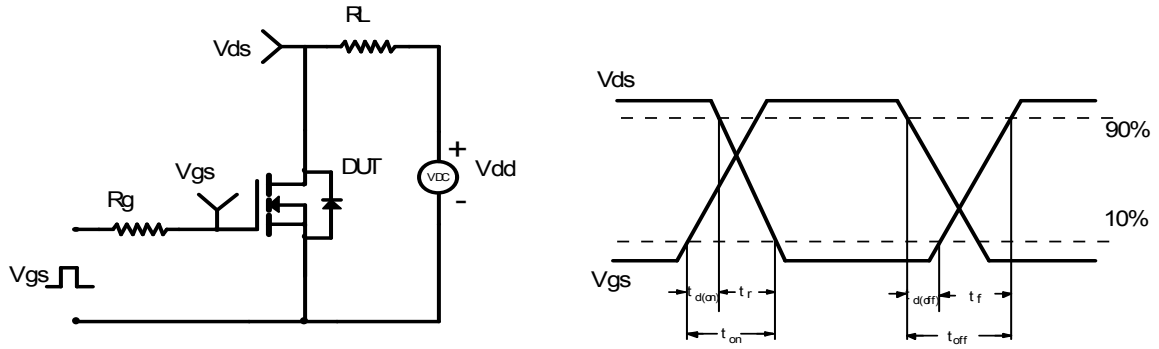


Figure 12: Normalized Maximum Transient Thermal Impedance

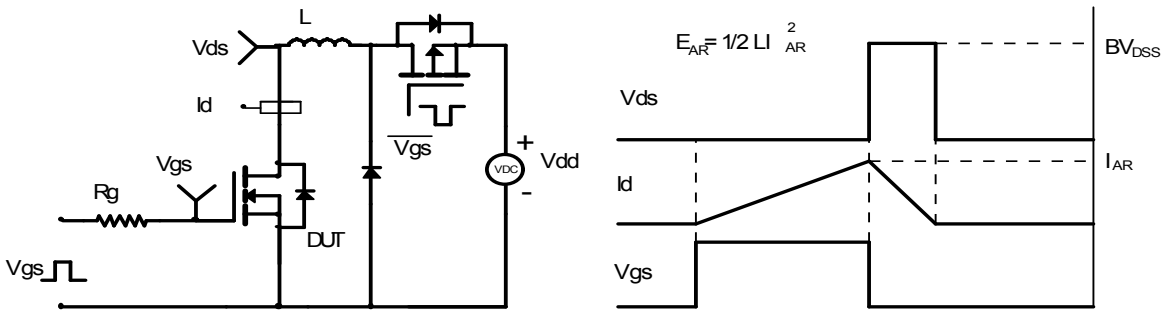
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms